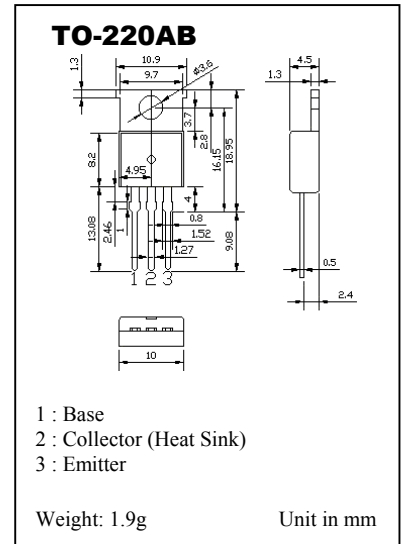


NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

...designed for use in horizontal output stages of video displays.

MAXIMUM RATINGS (T_c = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V _{CB0}	400	V
Collector Emitter Voltage	V _{CE0}	200	V
Emitter Base Voltage	V _{EBO}	6	V
Collector Current (DC)	I _C	8	A
Collector Current (Pulse)	I _{CP} *	15	A
Base Current	I _B	2	A
Collector Dissipation T _c = 25 °C	P _C	60	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C

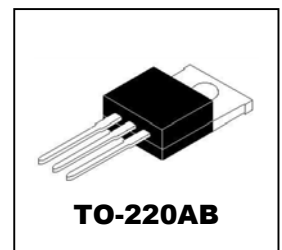


ELECTRICAL CHARACTERISTICS (T_c = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I _{CES}	V _{CE} = 400V, V _{BE} = 0	-	-	100	μA
Collector Cutoff Current	I _{CEV}	V _{CE} = 400V, V _{BE} = -6V	-	-	100	μA
Emitter Cutoff Current	I _{EBO}	V _{BE} = 6V, I _C = 0	-	-	3	mA
*Collector Emitter Saturation Voltage	V _{CE(sat)}	I _B = 50mA, I _C = 5A	-	-	1.5	V
*Base Emitter Saturation Voltage	V _{BE(sat)}	I _B = 50mA, I _C = 5A	-	-	2.4	V
*Collector Emitter Sustaining Voltage	V _{CE0(sus)}	I _B = 0, I _C = 100mA	200	-	-	V
*Damper Diode Forward Voltage	V _F	I _F = 4A	-	-	2	V

*Pulsed: pulsed duration = 300μs, duty cycle = 1.5%

**NPN EPITAXIAL
SILICON
DARLINGTON
TRANSISTOR**



PMC reserves the right to make changes without further notice to any products herein. **PMC** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **PMC** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential damages. The examples of applied circuits are provided as reference to the reader therefore we shall not undertake any responsibility for the exercise of rights by third parties.